

Claim 1 recites:

A method of forming a Spin-On-Glass (SOG) layer in an integrated circuit, the method comprising:

forming an SOG layer on an integrated circuit substrate;

performing a first curing process on the SOG layer;

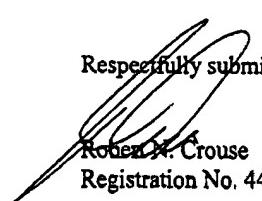
removing less than all of the SOG layer from the integrated circuit substrate through a mask pattern on the SOG layer to provide a remaining portion of the SOG layer on the integrated circuit substrate;

performing a second curing process on the remaining portion of the SOG layer; and

removing the remaining portion of the SOG layer to expose the integrated circuit substrate.

Applicants respectfully submit that Claim 1 reads on each of the species disclosed in the Application. For example, the fact that different embodiments of forming SOG layers according to the invention may use different gases in performing the first and second curing processes, does not mean that Claim 1 is not generic. To the contrary, the fact that Claim recites generic steps of first and second curing processes renders the claim generic to, for example, the different embodiments that use the different gases for curing. Accordingly, Applicants respectfully request that the Examiner acknowledge the generic nature of Claim 1, as this claim includes no material element additional to those recited in the species claims as set-out in the MPEP.

Respectfully submitted,


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